

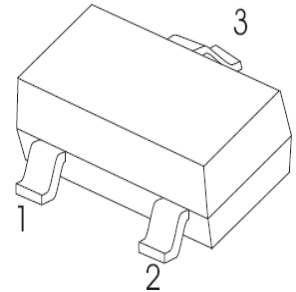
SOT-23 Plastic-Encapsulate Diodes

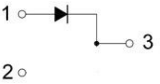
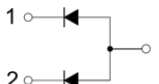
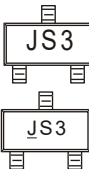
BAS21/A/C/S SWITCHING DIODE

FEATURES

- Fast Switching Speed
- Surface Mount Package Ideally Suited for Automatic Insertion
- For General Purpose Switching Applications
- FHigh Conductance

SOT-23



BAS21	BAS21A	BAS21C	BAS21S
			
MARKING: JS	MARKING:JS2	MARKING:JS3	MARKING:JS4
			

Solid dot = Green molding compound device, if none, the normal device

Maximum Ratings @Ta=25°C

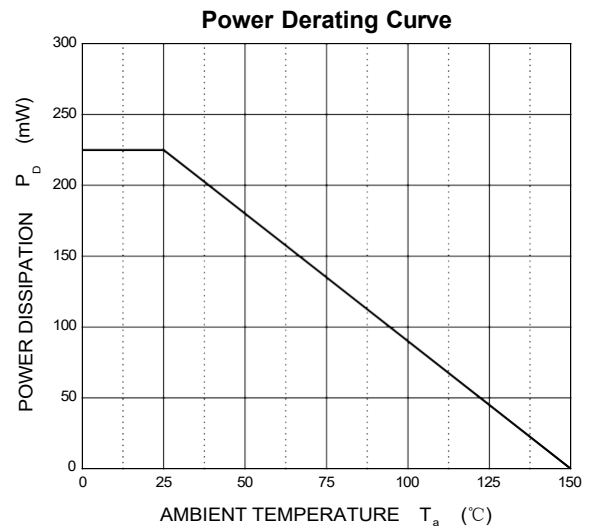
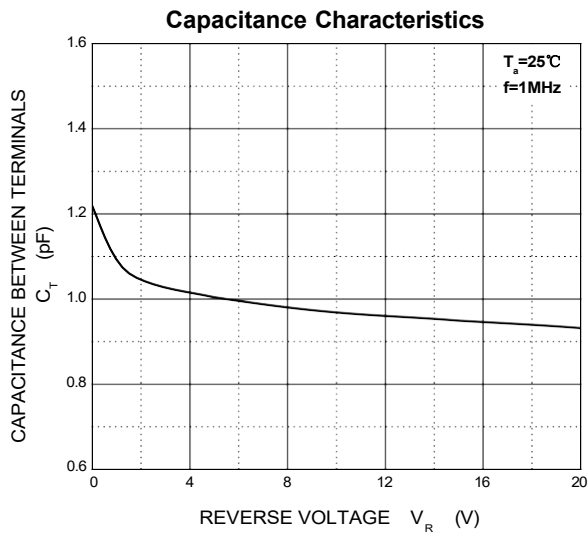
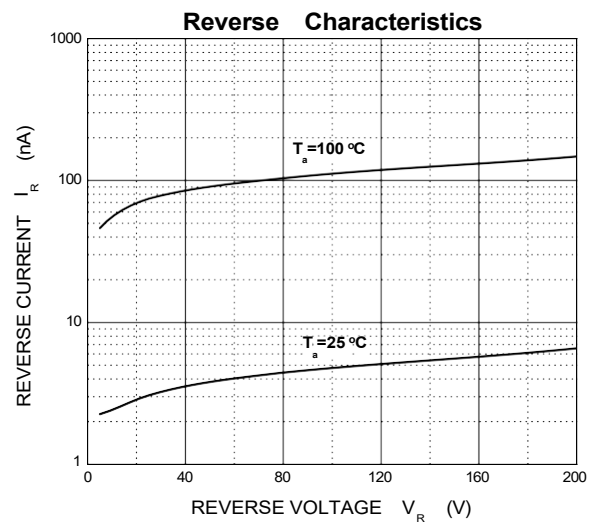
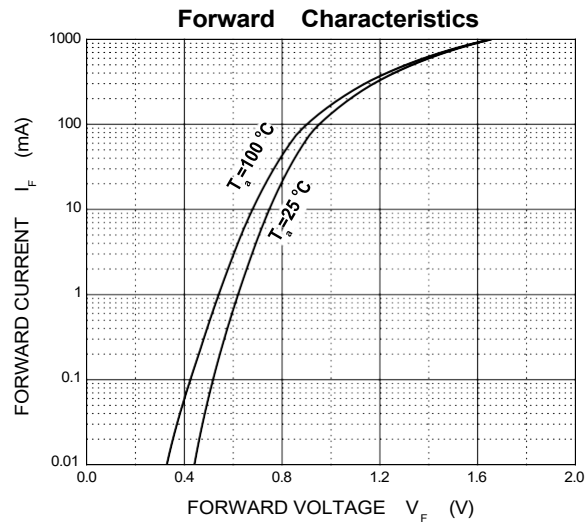
Parameter	Symbol	Limit	Unit
Repetitive peak reverse voltage	V_{RRM}	250	V
Working peak reverse voltage	V_{RWM}		
DC blocking voltage	V_R		
Forward continuous current	I_{FM}	400	mA
Average rectified output current	I_O	200	mA
Non-Repetitive Peak Forward Surge Current @t=8.3ms	I_{FSM}	2.5	A
Repetitive peak forward surge current	I_{FRM}	625	mA
Power dissipation	P_D	225	mW
Thermal resistance junction to ambient	$R_{\theta JA}$	555	°C/W
Junction temperature	T_J	150	°C
Storage temperature range	T_{STG}	-55~+150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R = 100\mu A$	250		V
Reverse voltage leakage current	I_R	$V_R = 200V$		0.1	μA
Forward voltage	V_F	$I_F = 100mA$ $I_F = 200mA$		1000 1250	mV
Diode capacitance	C_D	$V_R = 0V, f = 1MHz$		5	pF
Reveres recovery time	t_{rr}	$I_F = I_R = 30mA, I_{rr} = 0.1 \times I_R, R_L = 100\Omega$		50	ns

The above data are for reference only.

Typical Characteristics



The curve above is for reference only.